

FDMC8327L

N-Channel PowerTrench® MOSFET 40 V, 14 A, 9.7 mΩ

Features

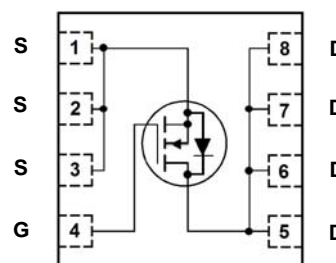
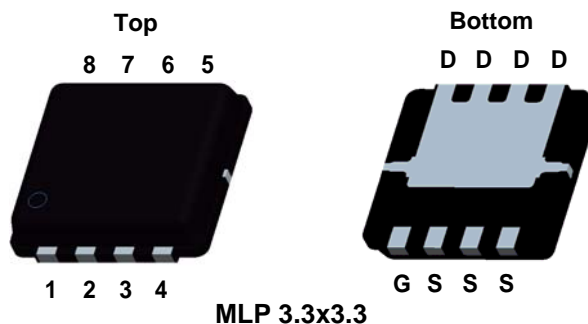
- Max $r_{DS(on)}$ = 9.7 mΩ at $V_{GS} = 10$ V, $I_D = 12$ A
- Max $r_{DS(on)}$ = 12.5 mΩ at $V_{GS} = 4.5$ V, $I_D = 10$ A
- Low Profile - 0.8mm max in Power 33
- 100% UIL test
- RoHS Compliant

General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Application

- DC-DC Conversion



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	40	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current - Continuous (Package limited) $T_C = 25^\circ\text{C}$	14	A
	- Continuous (Silicon limited) $T_C = 25^\circ\text{C}$	43	
	- Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	12	
	- Pulsed	60	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	25	mJ
P_D	Power Dissipation $T_C = 25^\circ\text{C}$	30	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case (Note 1)	4.2	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC8327L	FDMC8327L	Power 33	13"	12 mm	3000 units

Electrical Characteristics $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$	40			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^{\circ}\text{C}$		22		mV/ $^{\circ}\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 32\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0\text{ V}$			± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\text{ }\mu\text{A}$	1.0	1.7	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^{\circ}\text{C}$		-5		mV/ $^{\circ}\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$, $I_D = 12\text{ A}$		7.4	9.7	m Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 10\text{ A}$		9.4	12.5	
		$V_{GS} = 10\text{ V}$, $I_D = 12\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$		11	14.5	
g_{FS}	Forward Transconductance	$V_{DD} = 5\text{ V}$, $I_D = 12\text{ A}$		52		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 20\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		1235	1850	pF
C_{oss}	Output Capacitance			347	520	pF
C_{rss}	Reverse Transfer Capacitance			21	35	pF
R_g	Gate Resistance		0.1	0.6	1.3	Ω

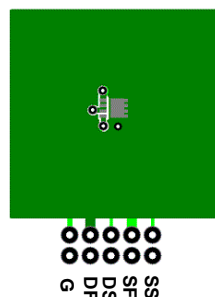
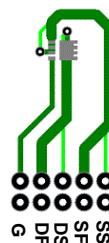
Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 20\text{ V}$, $I_D = 12\text{ A}$, $V_{GS} = 10\text{ V}$, $R_{GEN} = 6\text{ }\Omega$		8.4	17	ns
t_r	Rise Time			2.2	10	ns
$t_{d(off)}$	Turn-Off Delay Time			20	32	ns
t_f	Fall Time			2.2	10	ns
$Q_{g(TOT)}$	Total Gate Charge			18.5	26	nC
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0\text{ V}$ to 10 V	$V_{DD} = 20\text{ V}$, $I_D = 12\text{ A}$	9.7	14	nC
Q_{gs}	Gate to Source Charge	$V_{GS} = 0\text{ V}$ to 5 V		3.3		nC
Q_{gd}	Gate to Drain "Miller" Charge			2.6		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = 1.8\text{ A}$ (Note 2)		0.7	1.2	V
		$V_{GS} = 0\text{ V}$, $I_S = 12\text{ A}$ (Note 2)		0.8	1.3	
t_{rr}	Reverse Recovery Time	$I_F = 12\text{ A}$, $di/dt = 100\text{ A/s}$		32	51	ns
Q_{rr}	Reverse Recovery Charge			10	20	nC

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.a. 53 $^{\circ}\text{C/W}$ when mounted on a 1 in² pad of 2 oz copperb. 125 $^{\circ}\text{C/W}$ when mounted on a minimum pad of 2 oz copper2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.3. Starting $T_J = 25\text{ }^{\circ}\text{C}$; N-ch: $L = 0.3\text{ mH}$, $I_{AS} = 13\text{ A}$, $V_{DD} = 36\text{ V}$, $V_{GS} = 10\text{ V}$.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

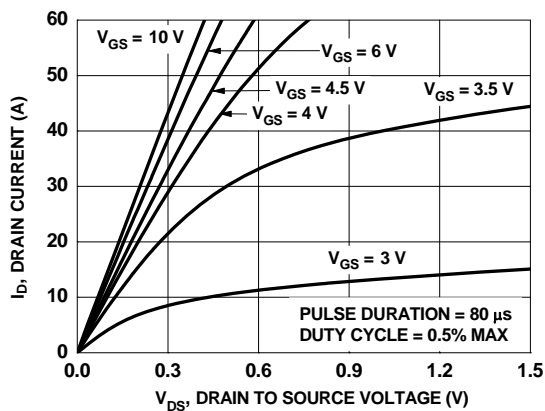


Figure 1. On Region Characteristics

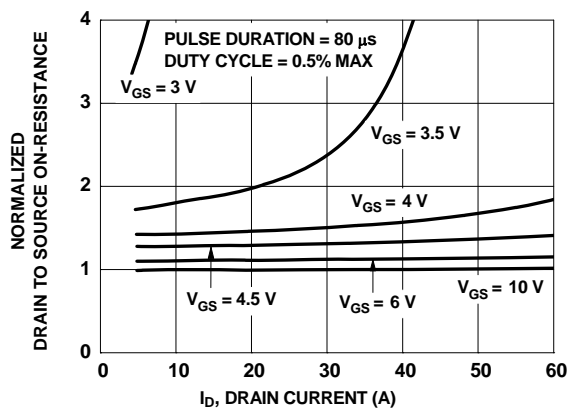


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

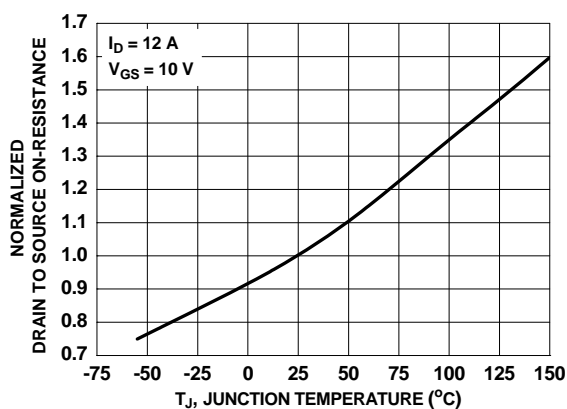


Figure 3. Normalized On Resistance vs Junction Temperature

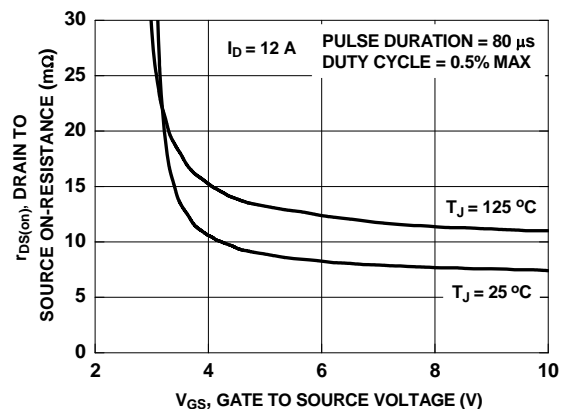


Figure 4. On-Resistance vs Gate to Source Voltage

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

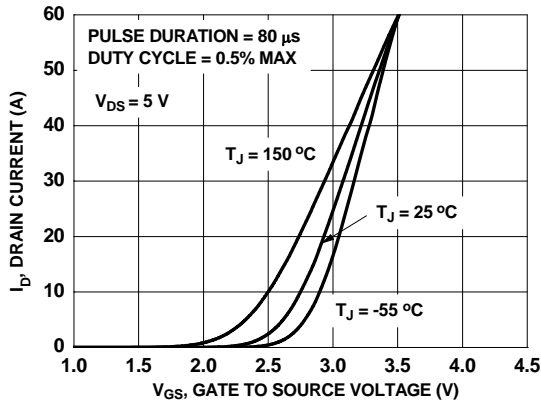


Figure 5. Transfer Characteristics

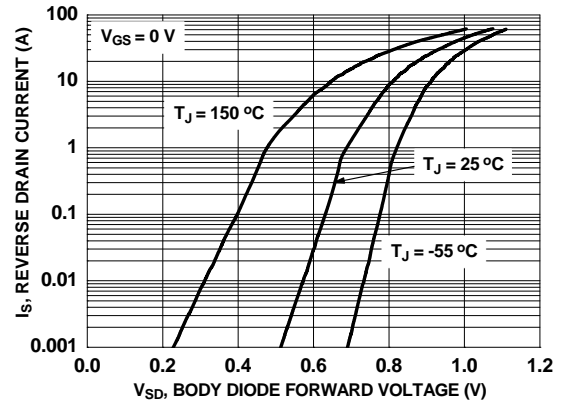


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

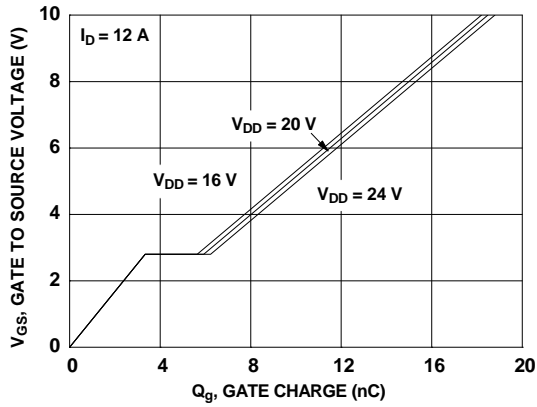


Figure 7. Gate Charge Characteristics

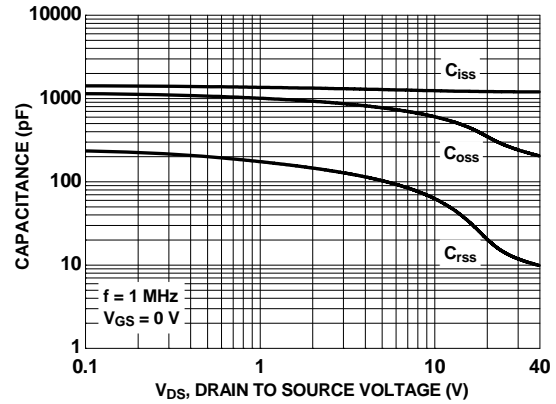


Figure 8. Capacitance vs Drain to Source Voltage

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

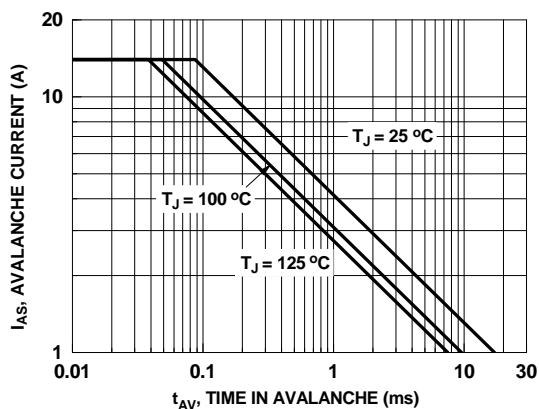


Figure 9. Unclamped Inductive Switching Capability

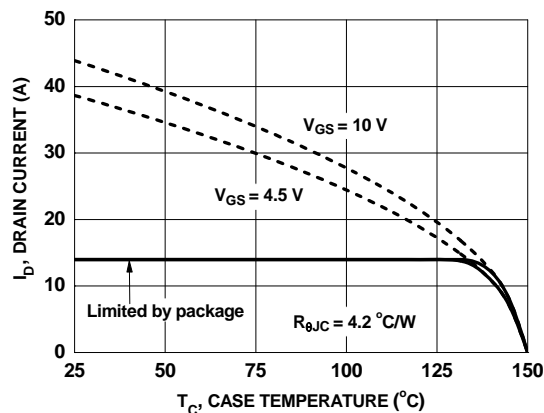


Figure 10. Maximum Continuous Drain Current vs Case Temperature

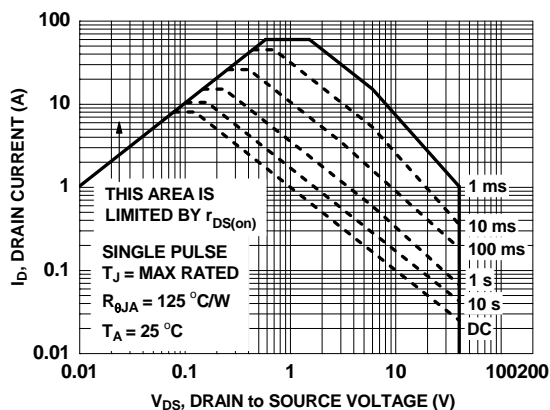


Figure 11. Forward Bias Safe Operating Area

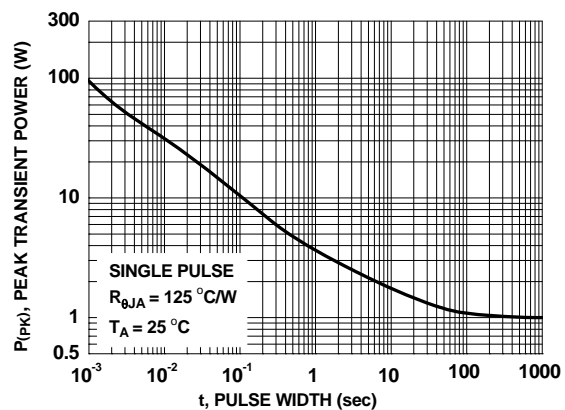
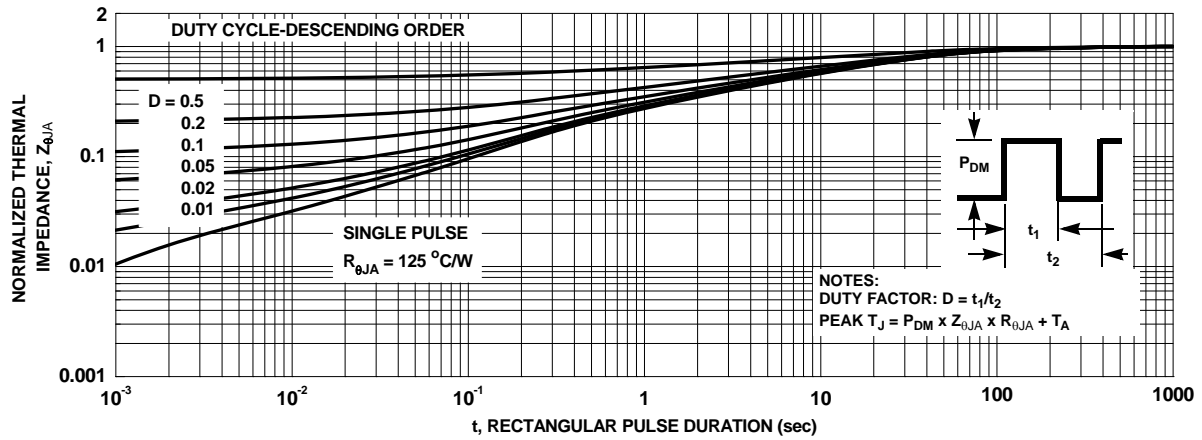
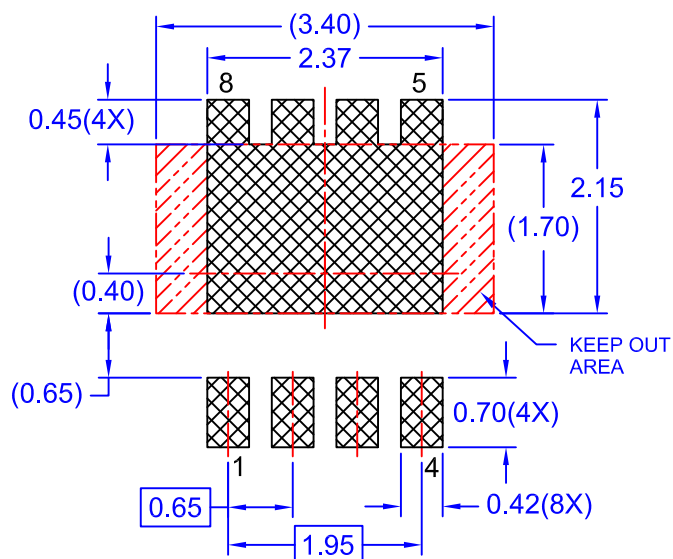
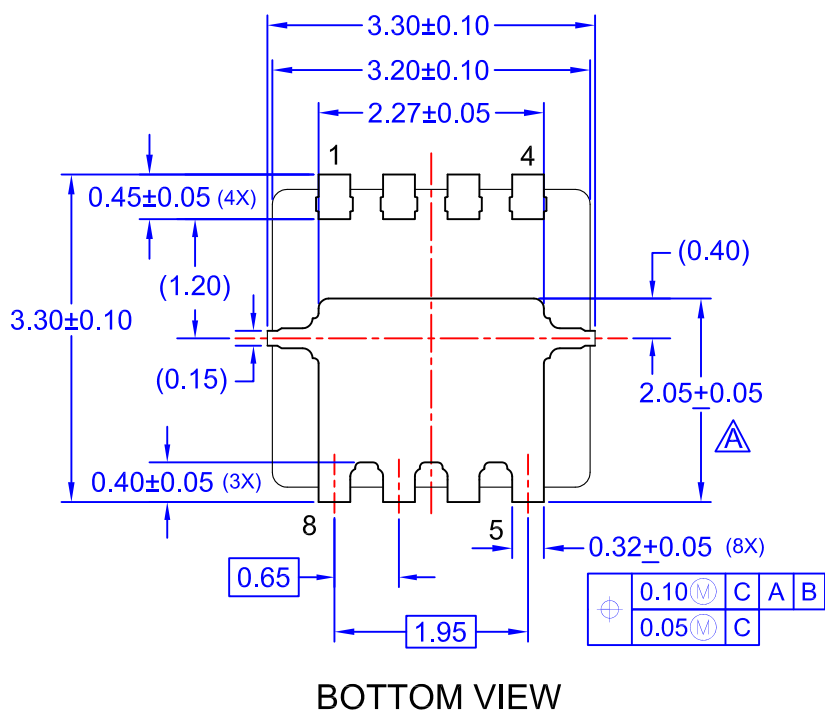
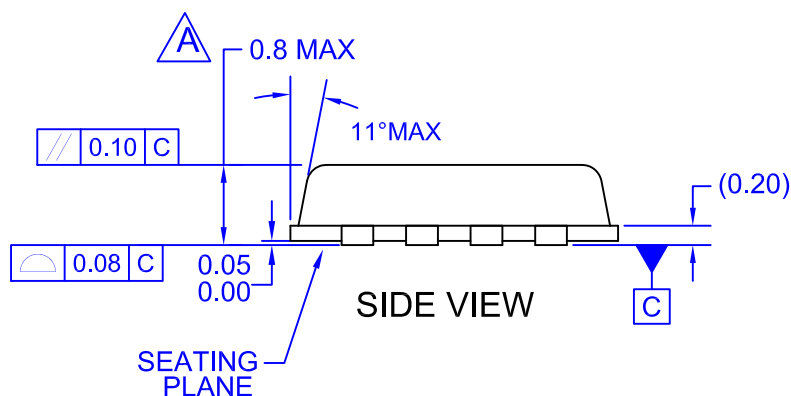
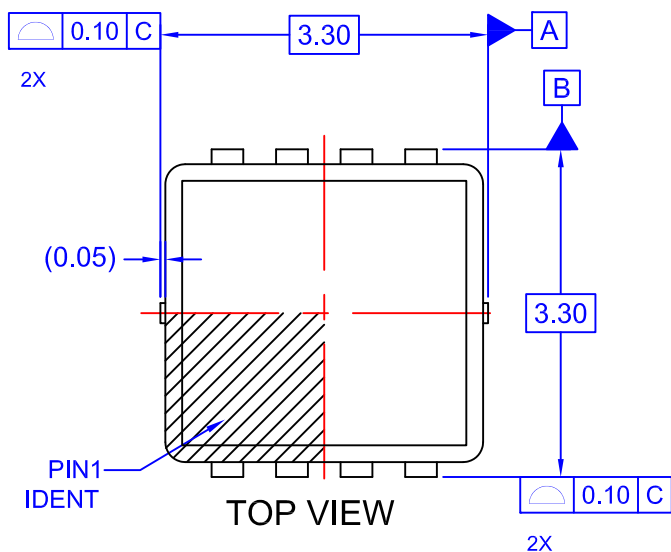


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted





NOTES:

- A. EXCEPT AS NOTED, PACKAGE CONFORMS TO JEDEC REGISTRATION MO-240 VARIATION BA.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. SEATING PLANE IS DEFINED BY TERMINAL TIPS ONLY
- E. BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH PROTRUSIONS NOR GATE BURRS.
- F. FLANGE DIMENSIONS INCLUDE INTERTERMINAL FLASH OR PROTRUSION. INTERTERMINAL FLASH OR PROTRUSION SHALL NOT EXCEED 0.25MM PER SIDE.
- G. IT IS RECOMMENDED TO HAVE NO TRACES OR VIA WITHIN THE KEEP OUT AREA.
- H. DRAWING FILENAME: MKT-MLP08Trev4.
- I. GENERAL RADII FOR ALL CORNERS SHALL BE 0.20MM MAX.



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